

General Description

The MDF10N65B MOSFET are produced using advanced MagnaChip's MOSFET Technology, which provides low on-state resistance, high switching performance and excellent quality.

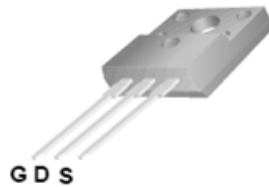
MDF10N65B is suitable device for SMPS, high Speed switching and general purpose applications.

Features

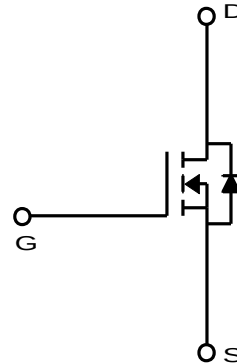
- $V_{DS} = 650V$
- $I_D = 10.0A$ @ $V_{GS} = 10V$
- $R_{DS(ON)} \leq 1.0\Omega$ @ $V_{GS} = 10V$

Applications

- Power Supply
- PFC
- High Current, High Speed Switching



TO-220F
MDF Series



Absolute Maximum Ratings ($T_a = 25^\circ C$)

Characteristics		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	650	V
Gate-Source Voltage		V_{GSS}	± 30	V
Continuous Drain Current	$T_C = 25^\circ C$	I_D	10.0*	A
	$T_C = 100^\circ C$		5.0*	A
Pulsed Drain Current ⁽¹⁾		I_{DM}	40*	A
Power Dissipation	$T_C = 25^\circ C$	P_D	47.7	W
	Derate above $25^\circ C$		0.38	W/ $^\circ C$
Repetitive Avalanche Energy ⁽¹⁾		E_{AR}	15	mJ
Peak Diode Recovery dv/dt ⁽³⁾		dv/dt	4.5	V/ns
Single Pulse Avalanche Energy ⁽⁴⁾		E_{AS}	212	mJ
Junction and Storage Temperature Range		T_J, T_{stg}	-55~150	$^\circ C$

* I_D limited by maximum junction temperature

Thermal Characteristics

Characteristics	Symbol	Rating	Unit
Thermal Resistance, Junction-to-Ambient ⁽¹⁾	$R_{\theta JA}$	62.5	$^\circ C/W$
Thermal Resistance, Junction-to-Case ⁽¹⁾	$R_{\theta JC}$	2.62	

Ordering Information

Part Number	Temp. Range	Package	Packing	RoHS Status
MDF10N65BTH	-55~150°C	TO-220F	Tube	Halogen Free

Electrical Characteristics (Ta =25°C)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	I _D = 250μA, V _{GS} = 0V	650	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	2.0	-	4.0	
Drain Cut-Off Current	I _{DSS}	V _{DS} = 650V, V _{GS} = 0V	-	-	1	μA
Gate Leakage Current	I _{GSS}	V _{GS} = ±30V, V _{DS} = 0V	-	-	100	nA
Drain-Source ON Resistance	R _{DS(ON)}	V _{GS} = 10V, I _D = 4A		0.85	1.0	Ω
Forward Transconductance	g _{fs}	V _{DS} = 30V, I _D = 4A	-	10.6	-	S
Dynamic Characteristics						
Total Gate Charge	Q _g	V _{DS} = 520V, I _D = 8.0A, V _{GS} = 10V ⁽³⁾	-	29.3	-	nC
Gate-Source Charge	Q _{gs}		-	7.0	-	
Gate-Drain Charge	Q _{gd}		-	11.2	-	
Input Capacitance	C _{iss}	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz	-	1202	-	pF
Reverse Transfer Capacitance	C _{rss}		-	7.08	-	
Output Capacitance	C _{oss}		-	128.3	-	
Turn-On Delay Time	t _{d(on)}	V _{GS} = 10V, V _{DS} = 325V, I _D = 8.0A, R _G = 25Ω ⁽³⁾	-	19.4	-	Ns
Rise Time	t _r		-	48	-	
Turn-Off Delay Time	t _{d(off)}		-	96.5	-	
Fall Time	t _f		-	49	-	
Drain-Source Body Diode Characteristics						
Maximum Continuous Drain to Source Diode Forward Current	I _S		-	8	-	A
Source-Drain Diode Forward Voltage	V _{SD}	I _S = 8.0A, V _{GS} = 0V	-	-	1.4	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = 8.0A, dI/dt = 100A/μs ⁽³⁾	-	326	-	ns
Body Diode Reverse Recovery Charge	Q _{rr}		-	5.9	-	μC

Note :

1. Pulse width is based on $R_{\theta JC}$ & $R_{\theta JA}$ and the maximum allowed junction temperature of 150°C.
2. Pulse test: pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$, pulse width limited by junction temperature $T_{J(MAX)}=150^\circ C$.
3. $I_{SD} \leq 8.0A$, $di/dt \leq 200A/\mu s$, $V_{DD}=50V$, $R_g = 25\Omega$, Starting $T_J=25^\circ C$
4. $L=7.0mH$, $I_{AS}=8.0A$, $V_{DD}=50V$, $R_g = 25\Omega$, Starting $T_J=25^\circ C$,

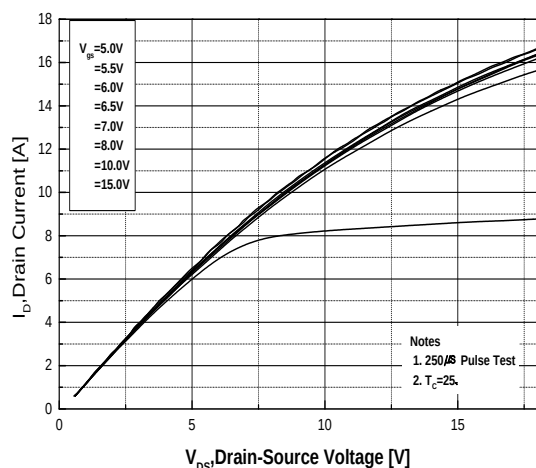


Fig.1 On-Region Characteristics

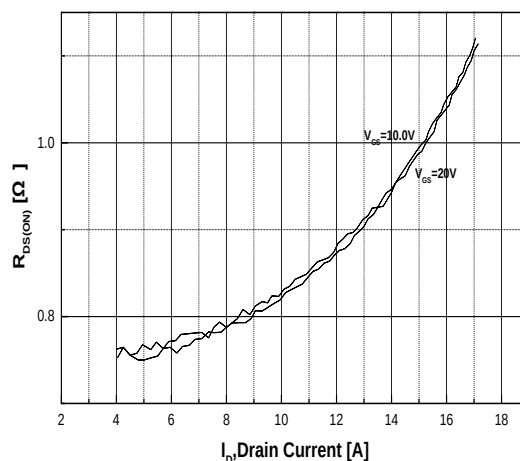


Fig.2 On-Resistance Variation with Drain Current and Gate Voltage

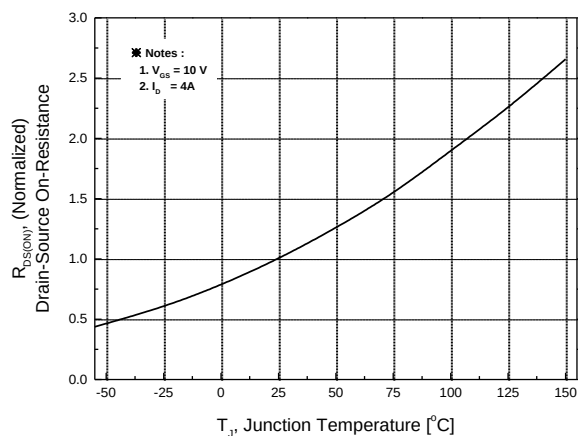


Fig.3 On-Resistance Variation with Temperature

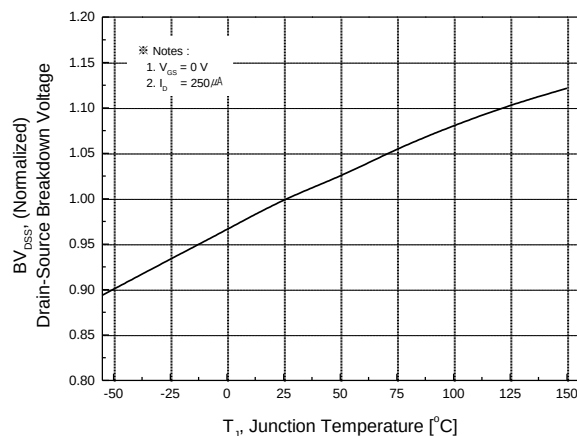


Fig.4 Breakdown Voltage Variation vs. Temperature

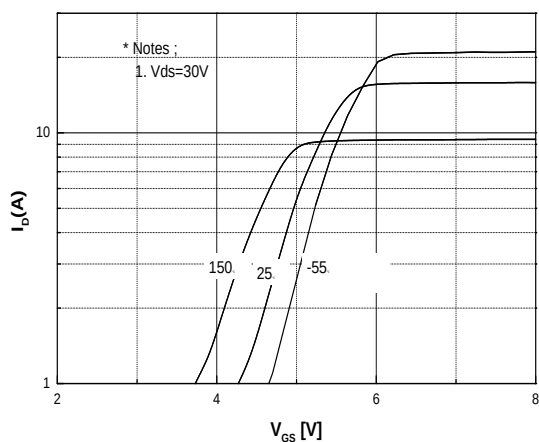


Fig.5 Transfer Characteristics

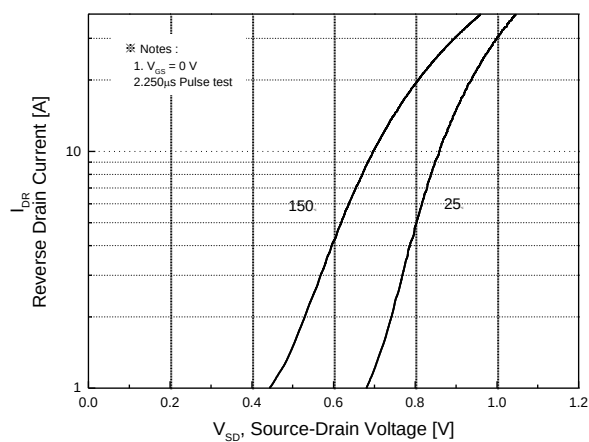
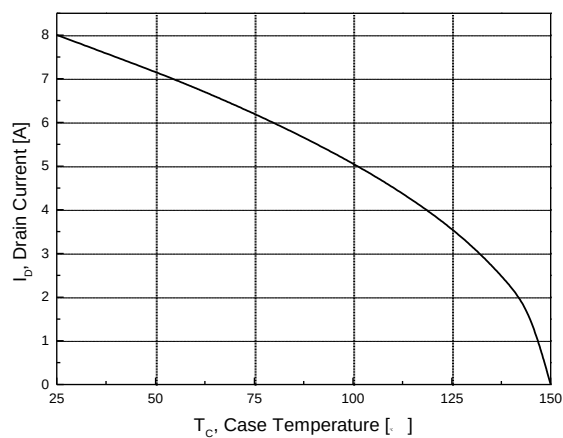
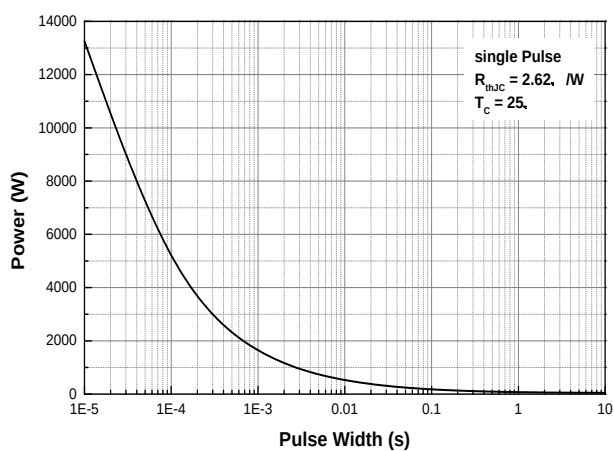
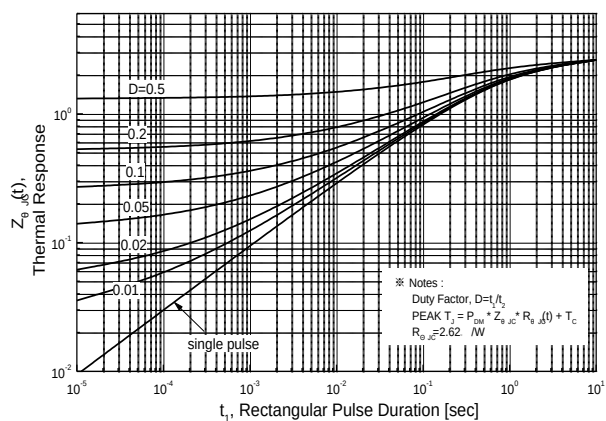
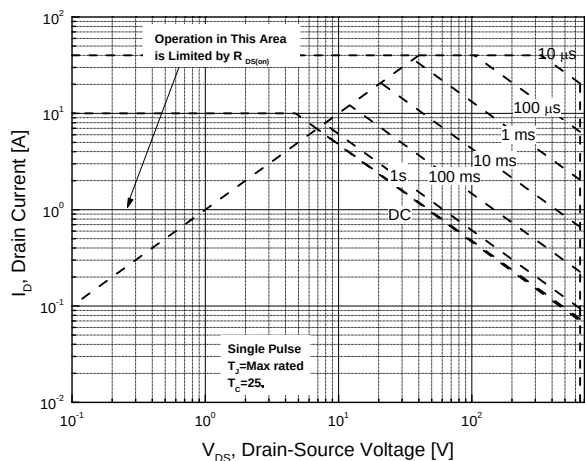
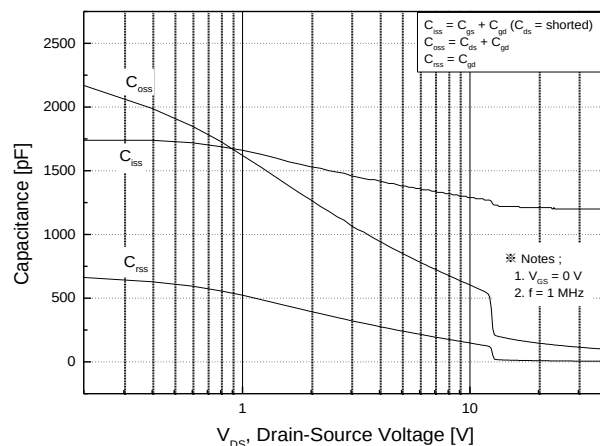
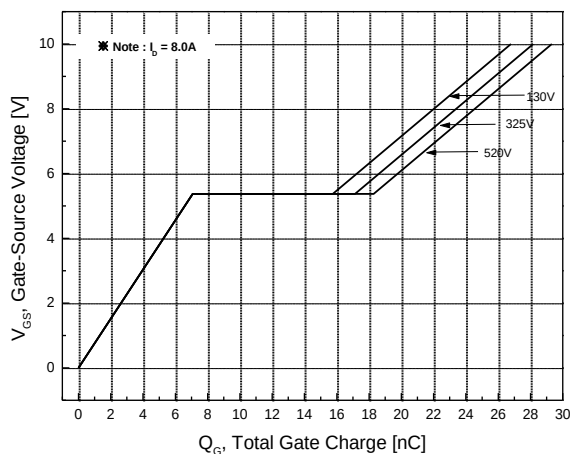


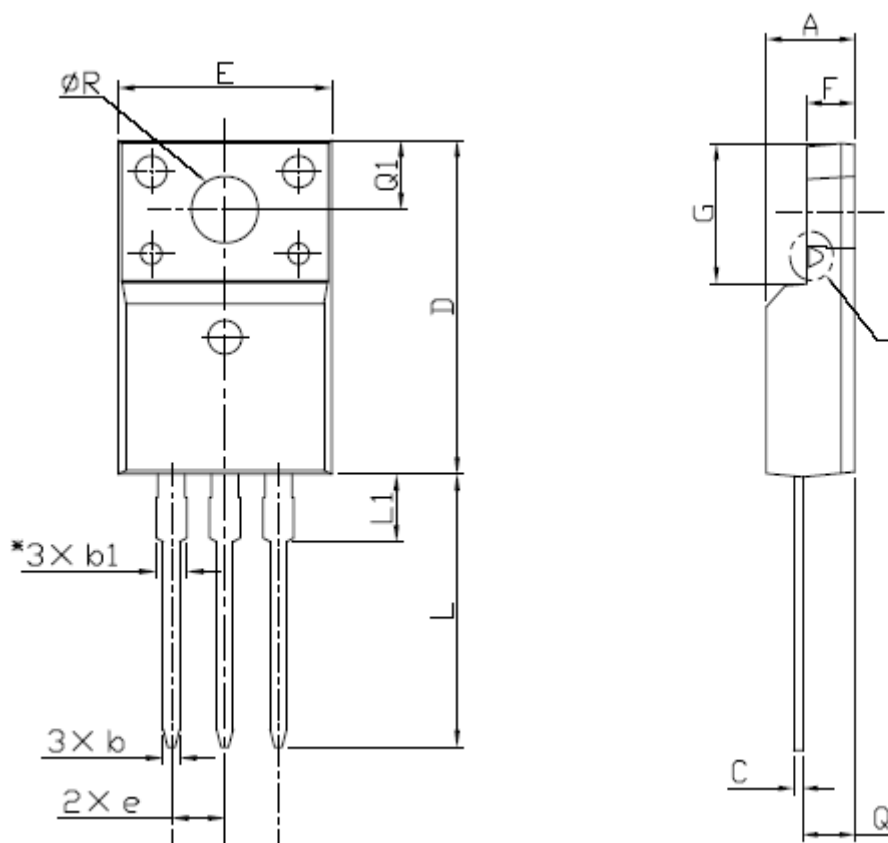
Fig.6 Body Diode Forward Voltage Variation with Source Current and Temperature



Physical Dimensions

3 Leads, TO-220F

Dimensions are in millimeters unless otherwise specified



Symbol	Min	Nom	Max
A	4.50		4.93
b	0.63		0.91
b1	1.15		1.47
C	0.33		0.63
D	15.47		16.13
E	9.60		10.71
e		2.54	
F	2.34		2.84
G	6.48		6.90
L	12.24		13.72
L1	2.79		3.67
Q	2.52		2.96
Q1	3.10		3.50
ØR	3.00		3.55

DISCLAIMER:

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